<b>ESRF</b>	<b>Experiment title:</b> Real-time simultaneous study of optical spectra and film structure of organic semiconductors during growth	<b>Experiment</b> <b>number</b> : SI-1936
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## Report:

## **1. Introduction**

As described in the proposal, the purpose of the experiments at ID10B was to study the relationship between optical and structural properties of organic semiconductor thin films, especially from sub-monolayer coverage. Both properties are crucial for organic devices, such as organic photovoltaic cells and organic light-emitting diodes, and also are of great fundamental interest because they are often strongly coupled to each other. The experiment was performed using our new home-made portable UHV chamber which allows simultaneous X-ray and optical measurements.

The *in situ* real-time measurements of X-ray reflectivity (XRR) and differential reflectance spectroscopy (DRS) were performed on perfluorinated copper phthalocyanine ( $F_{16}CuPc$ ) and  $H_{16}CuPc$  thin films deposited on a SiO<sub>2</sub>/Si wafer. The DRS technique, which determines the light absorption of the films with sub-monolayer sensitivity [1], was combined with real-time XRR measurements [2]. The materials are typical examples of n- or p-type semiconductors, respectively. The molecules proposed for this beamtime, i.e. perfluorinated pentacene and pentacene, were replaced by the two phthalocyanine derivatives, because test experiments with  $F_{16}CuPc$  on SiO<sub>2</sub> had shown unusual spectral changes, that might be related to structural transitions accessible via real-time XRR.

Below we give a short summary of the results for one of systems, namely  $F_{16}CuPc/SiO_2$ , obtained in the beamtime (SI-1936) at ID10B.



Fig. 1 Chemical structure of  $F_{16}CuPc$ 

## 2. Real-time X-ray reflectivity measurements of F<sub>16</sub>CuPc/SiO<sub>2</sub>



Real-time XRR data of  $F_{16}$ CuPc deposited on SiO<sub>2</sub> at 303 K are shown in Fig. 2(a). In the post-growth reflectivity data we observe the well-known first-order Bragg peak at  $q_{Bragg}$ =0.42 Å<sup>-1</sup>, which corresponds to a lattice plane spacing of 1.50 nm and essentially standing  $F_{16}$ CuPc molecules. From the real-time results the reflectivity at the anti-Bragg point, i.e. at  $q_{Bragg}/2$ , can be extracted. The data are shown in Fig. 2(b) as a function of the film thickness, which we determined separately by fitting the XRR data.

Above  $\Delta \approx 2.1$  nm we find the expected growth oscillations with a periodicity of 1.50 nm and a strong damping. Our data indicate that the molecules form layered films of standing molecules with a significant roughness. However, the observed  $\Delta$ -value is larger than the lattice spacing of standing molecules. This has been explained before [4] by the nucleation of one monolayer of standing molecules (1.50 nm) on an interface layer consisting of two layers of lying F<sub>16</sub>CuPc molecules (2 x 0.7 nm).

FIG. 2: (a) Evolution of the real-time XRR of  $F_{16}CuPc$  thin films as a function of time (film thickness) during growth on SiO<sub>2</sub> at 303 K. (b) Thickness-dependent reflectivity at the anti-Bragg-point ( $q_{Bragg}/2$ ) extracted from (a). The film thickness was obtained by fitting the reflectivity curves with Parratt's formalism.

# 3. Evolution of DRS spectra correlated to thickness-dependent structural transition

DRS spectra for selected film thicknesses with the corresponding numbers of molecular layers (ML) are shown in Fig. 3(a). Due to the structural transition of  $F_{16}CuPc/SiO_2$  a significant variation of the spectra – especially below 2 ML – is observed. An absorption feature A and a broad shoulder B, which becomes dominant at 1 ML, are observed at 1.82 eV and 1.96 eV, respectively. In addition, a third feature C around 1.59 eV appears at 1 ML and becomes more intense with increasing film thickness.

In the literature the absorption spectra of  $F_{16}$ CuPc thin films have been discussed based on molecular exciton theory [5]. Therein, peak C is attributed to the  $\beta$ -phase of  $F_{16}$ CuPc, that is characterized by ring-over-ring (eclipsed)  $\pi$ -orbital stackings and an inclined alignment of the transition dipoles, see Fig. 3(b).<sup>†</sup> Schlettwein et al. [7] have noted that for  $F_{16}$ ZnPc growth on glass substrates feature A is at similar energies as a peak found in solution spectra, suggesting that this feature could be related to an amorphous  $F_{16}$ ZnPc phase in the film.

With these information and on the basis of the XRR data taken during this beamtime the changes in the DRS spectra can be explained:

- Initially, the molecules prefer the flat-lying orientation and form an amorphous film with spectra showing mainly feature A.
- After completion of the interface layer the molecules build up the bilayer structure reported in Ref. [4] with nearly parallel transition dipole moments, causing the observed increase of feature B.
- Finally, the thin film  $\beta$ -phase of  $F_{16}$ ZnPc with the typical growth oscillations starts to nucleate. Above 2 ML the corresponding feature C appears in the spectra

<sup>&</sup>lt;sup>†</sup> Peak C, in contrast, is not observed for the columnar  $\alpha$ -CuPc structure with parallel transition dipole moments [6].

### 5. Summary



FIG. 3: (a) Q-band region for selected DRS spectra of  $F_{16}CuPc$  on  $SiO_2$ , which correspond to the film thickness given in Fig. 2(b). The intensity of the spectra was multiplied arbitrarily for a better of an evolution of the spectral shape. (b) A schematic of the angle  $\theta$  between the transition dipole moments in a molecular column of the bilayer-phase and -phase estimated in Ref. [4].

#### 5. References

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We studied the thickness-dependent absorption spectra of F<sub>16</sub>CuPc thin films deposited on SiO<sub>2</sub> during growth simultaneously with measuring the real-time X-ray reflectivity. We confirmed the reported thickness dependent structural transition and determined the corresponding absorption spectra from the monolayer regime.

We demonstrated that simultaneous *in situ* realtime XRR/DRS measurements are a powerful approach to understand in which way the optical properties of organic thin films are related to the film structure and the growth behaviour.

A publication with the results for F<sub>16</sub>CuPc/SiO<sub>2</sub> will appear shortly [2]. – We wish to thank our local contact for the excellent support on ID10B.